# VS-12TTS08PbF, VS-12TTS08-M3

# Vishay Semiconductors

| ABSOLUTE MAXIMUM RATINGS                  |                                  |   |        |                  |  |  |  |
|---|----------------------------------|---|--------|------------------|--|--|--|
| PARAMETER                                 | SYMBOL                           | TEST CONDITIONS   | VALUES | UNITS            |  |  |  |
| Maximum average on-state current          | I <sub>T(AV)</sub>               | T <sub>C</sub> = 108 °C, 180° conduction, half sine wave  | 8      |                  |  |  |  |
| Maximum RMS on-state current              | I <sub>T(RMS)</sub>              | 1°C = 100°C, 100°COHQUCTION, Hall Sine wave   | 12.5   |                  |  |  |  |
| Maximum peak, one-cycle,                  | <b>I</b>                         | 10 ms sine pulse, rated $V_{RRM}$ applied, $T_J$ = 125 °C   | 95     | Α                |  |  |  |
| non-repetitive surge current              | I <sub>TSM</sub>                 | 10 ms sine pulse, no voltage reapplied, T <sub>J</sub> = 125 °C                                     | 110    | <br>             |  |  |  |
| Maximum I <sup>2</sup> t for fusing       | l <sup>2</sup> t                 | 10 ms sine pulse, rated V <sub>RRM</sub> applied, T <sub>J</sub> = 125 °C                           | 45     | A <sup>2</sup> s |  |  |  |
| Maximum i-t for fusing                    | 1-1                              | 10 ms sine pulse, no voltage reapplied, T <sub>J</sub> = 125 °C                                     | 64     |                  |  |  |  |
| Maximum I <sup>2</sup> √t for fusing      | I²√t                             | $t=0.1$ ms to 10 ms, no voltage reapplied, $T_J=125~^{\circ}C$                                      | 640    | A²√s             |  |  |  |
| Maximum on-state voltage drop             | V <sub>TM</sub>                  | 8 A, T <sub>J</sub> = 25 °C   | 1.2    | V                |  |  |  |
| On-state slope resistance                 | r <sub>t</sub>                   | T <sub>.1</sub> = 125 °C  | 16.2   | mΩ               |  |  |  |
| Threshold voltage                         | V <sub>T(TO)</sub>               | 1j=125 C  | 0.87   | V                |  |  |  |
| Maximum reverse and direct leakage        | 1 /1                             | $T_J = 25 ^{\circ}\text{C}$   | 0.05   |                  |  |  |  |
| current                                   | I <sub>RM</sub> /I <sub>DM</sub> | $T_{J} = 125  ^{\circ}\text{C}$ $V_{R} = \text{Rated } V_{RRM}/V_{DRM}$                             | 1.0    |                  |  |  |  |
| Typical holding current                   | I <sub>H</sub>                   | Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C                              | 30     | mA               |  |  |  |
| Maximum latching current                  | ΙL                               | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C  | 50     |                  |  |  |  |
| Maximum rate of rise of off-state voltage | dV/dt                            | $T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C, } V_{DRM} = R_g ^{-}\text{k} = \text{Open}$ | 150    | V/µs             |  |  |  |
| Maximum rate of rise of turned-on current | dl/dt                            |   | 100    | A/μs             |  |  |  |

| TRIGGERING                                  |                    |  |        |       |  |
|---|--------------------|--|--------|-------|--|
| PARAMETER                                   | SYMBOL             | TEST CONDITIONS  | VALUES | UNITS |  |
| Maximum peak gate power                     | P <sub>GM</sub>    |  | 8.0    | W     |  |
| Maximum average gate power                  | P <sub>G(AV)</sub> |  | 2.0    | VV    |  |
| Maximum peak positive gate current          | + I <sub>GM</sub>  |  | 1.5    | Α     |  |
| Maximum peak negative gate voltage          | - V <sub>GM</sub>  |  | 10     | V     |  |
|   | I <sub>GT</sub>    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C | 20     | mA    |  |
| Maximum required DC gate current to trigger |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 15     |       |  |
| Linggoi                                     |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 10     |       |  |
|   | V <sub>GT</sub>    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C | 1.2    |       |  |
| Maximum required DC gate voltage to trigger |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 1      | V     |  |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 0.7    | V     |  |
| Maximum DC gate voltage not to trigger      | $V_{GD}$           | T = 105 °C V = Poted value                                   | 0.2    |       |  |
| Maximum DC gate current not to trigger      | I <sub>GD</sub>    | T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value      | 0.1    | mA    |  |

| SWITCHING                     |                 |                          |        |       |  |
|-------------------------------|-----------------|--------------------------|--------|-------|--|
| PARAMETER                     | SYMBOL          | TEST CONDITIONS          | VALUES | UNITS |  |
| Typical turn-on time          | t <sub>gt</sub> | T <sub>J</sub> = 25 °C   | 0.8    |       |  |
| Typical reverse recovery time | t <sub>rr</sub> | T <sub>.1</sub> = 125 °C | 3      | μs    |  |
| Typical turn-off time         | t <sub>q</sub>  | 1j = 125 C               | 100    |       |  |



#### www.vishay.com

## Vishay Semiconductors

| THERMAL AND MECHANICAL SPECIFICATIONS           |         |                                   |                                      |             |            |  |
|---|---------|-----------------------------------|--------------------------------------|-------------|------------|--|
| PARAMETER                                       |         | SYMBOL                            | IBOL TEST CONDITIONS                 |             | UNITS      |  |
| Maximum junction and storage temperature range  |         | T <sub>J</sub> , T <sub>Stg</sub> |                                      | - 40 to 125 | °C         |  |
| Maximum thermal resistance, junction to case    |         | R <sub>thJC</sub>                 | DC operation                         | 1.5         |            |  |
| Maximum thermal resistance, junction to ambient |         | R <sub>thJA</sub>                 |                                      | 62 °C/W     |            |  |
| Typical thermal resistance, case to heatsink    |         | R <sub>thCS</sub>                 | Mounting surface, smooth and greased | 0.5         |            |  |
| Approximate weight                              |         |                                   |                                      | 2           | g          |  |
| Approximate weight                              |         |                                   |                                      | 0.07        | OZ.        |  |
| Mounting torque                                 | minimum |                                   |                                      | 6 (5)       | kgf · cm   |  |
|   | maximum |                                   |                                      | 12 (10)     | (lbf · in) |  |
| Marking device                                  |         |                                   | Case style TO-220AB 12TTS08          |             | S08        |  |

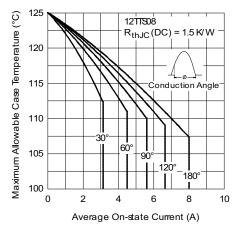


Fig. 1 - Current Ratings Characteristics

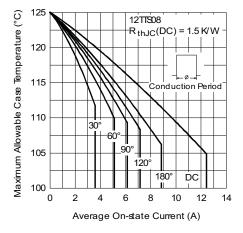


Fig. 2 - Current Ratings Characteristics

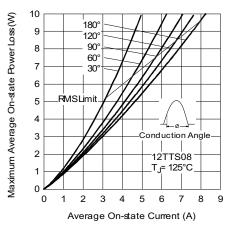


Fig. 3 - On-State Power Loss Characteristics

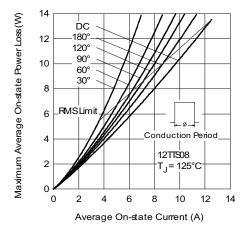


Fig. 4 - On-State Power Loss Characteristics

## Vishay Semiconductors

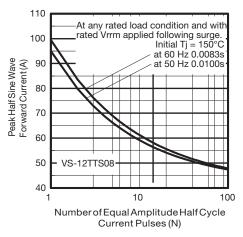


Fig. 5 - Maximum Non-Repetitive Surge Current

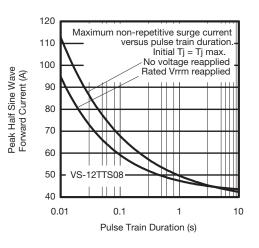


Fig. 6 - Maximum Non-Repetitive Surge Current

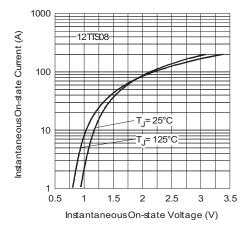


Fig. 7 - On-State Voltage Drop Characteristics

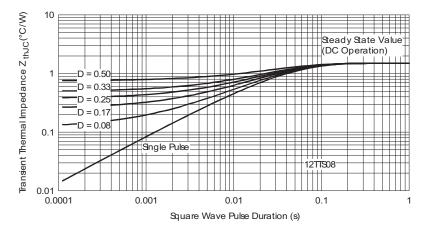


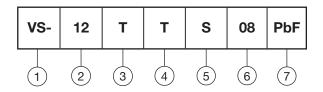
Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

# VS-12TTS08PbF, VS-12TTS08-M3

### Vishay Semiconductors

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current ratings (12 = 12.5 A)

- Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220

5 - Type of silicon

S = Standard recovery rectifier

6 - Voltage rating (08 = 800 V)

- Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) |                  |                        |                          |  |  |  |
|--------------------------------|------------------|------------------------|--------------------------|--|--|--|
| PREFERRED P/N                  | QUANTITY PER T/R | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION    |  |  |  |
| VS-12TTS08PbF                  | 50               | 1000                   | Antistatic plastic tubes |  |  |  |
| VS-12TTS08-M3                  | 50               | 1000                   | Antistatic plastic tubes |  |  |  |

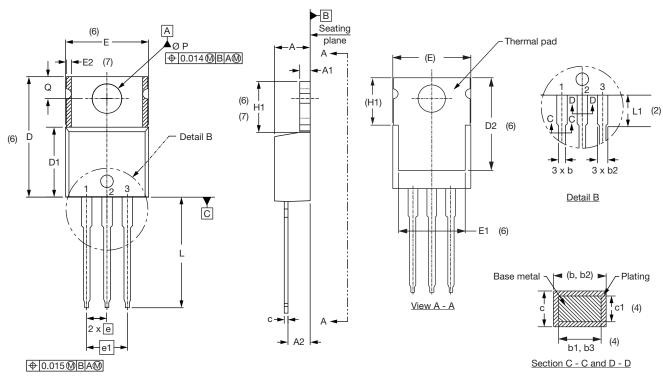
| LINKS TO RELATED DOCUMENTS                 |              |                          |  |  |
|--|--------------|--------------------------|--|--|
| Dimensions <u>www.vishay.com/doc?95222</u> |              |                          |  |  |
| Part marking information                   | TO-220AB PbF | www.vishay.com/doc?95225 |  |  |
|  | TO-220AB -M3 | www.vishay.com/doc?95028 |  |  |



### Vishay Semiconductors

### **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



### Lead assignments

#### <u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

### Conforms to JEDEC outline TO-220AB

| SYMBOL | MILLIMETERS |       | INC   | NOTES |       |
|--------|-------------|-------|-------|-------|-------|
| STMBOL | MIN.        | MAX.  | MIN.  | MAX.  | NOTES |
| Α      | 4.25        | 4.65  | 0.167 | 0.183 |       |
| A1     | 1.14        | 1.40  | 0.045 | 0.055 |       |
| A2     | 2.56        | 2.92  | 0.101 | 0.115 |       |
| b      | 0.69        | 1.01  | 0.027 | 0.040 |       |
| b1     | 0.38        | 0.97  | 0.015 | 0.038 | 4     |
| b2     | 1.20        | 1.73  | 0.047 | 0.068 |       |
| b3     | 1.14        | 1.73  | 0.045 | 0.068 | 4     |
| С      | 0.36        | 0.61  | 0.014 | 0.024 |       |
| c1     | 0.36        | 0.56  | 0.014 | 0.022 | 4     |
| D      | 14.85       | 15.25 | 0.585 | 0.600 | 3     |
| D1     | 8.38        | 9.02  | 0.330 | 0.355 |       |
| D2     | 11.68       | 12.88 | 0.460 | 0.507 | 6     |

| SYMBOL  | MILLIMETERS |       | INC        | NOTES |       |
|---------|-------------|-------|------------|-------|-------|
| STIMBOL | MIN.        | MAX.  | MIN.       | MAX.  | NOTES |
| Е       | 10.11       | 10.51 | 0.398      | 0.414 | 3, 6  |
| E1      | 6.86        | 8.89  | 0.270      | 0.350 | 6     |
| E2      | -           | 0.76  | -          | 0.030 | 7     |
| е       | 2.41        | 2.67  | 0.095      | 0.105 |       |
| e1      | 4.88        | 5.28  | 0.192      | 0.208 |       |
| H1      | 6.09        | 6.48  | 0.240      | 0.255 | 6, 7  |
| L       | 13.52       | 14.02 | 0.532      | 0.552 |       |
| L1      | 3.32        | 3.82  | 0.131      | 0.150 | 2     |
| ØΡ      | 3.54        | 3.73  | 0.139      | 0.147 |       |
| Q       | 2.60        | 3.00  | 0.102      | 0.118 |       |
| θ       | 90° to 93°  |       | 90° to 93° |       |       |
|         |             |       |            |       |       |

### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip

## **Legal Disclaimer Notice**



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